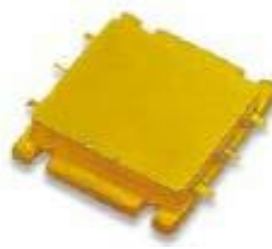


Performance

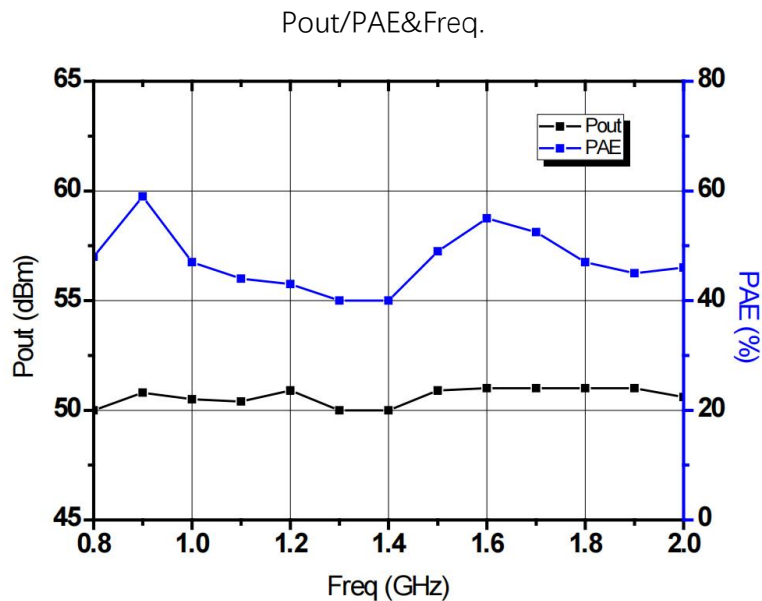
- Technology: 0.25um Power GaN HEMT
- Frequency: 0.8~2.0GHz
- Typical Pout : 50dBm(CW)
- Typical Gain: 10dB
- Typical PAE: 45%
- Bias: 28V/-2.2V
- Package: Metal Ceramic



Electrical Specifications (TA=25°C, Vd=28V, Vg= -2.2V, F: 0.8~2.0GHz)

Symbol	Parameter	Min	Typical	Max	Unit
Pout	Output Power	49.8	50	-	dBm
Gp	Power Gain	-	10	-	dB
η_{add}	Power Added Efficiency	40	45	-	%
ΔGp	Gain Flatness	-0.8	-	+0.8	dB

Test Curves

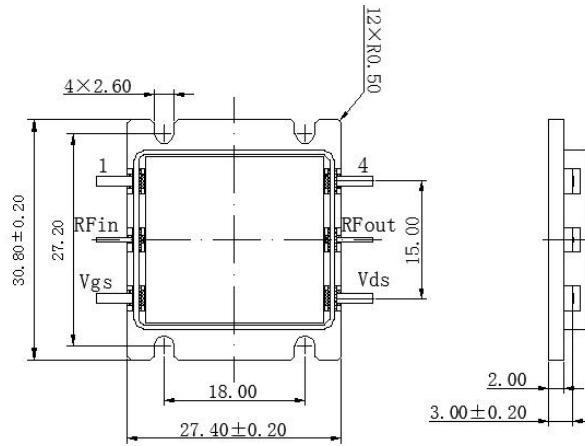


Absolute Max Ratings (TA=25°C)

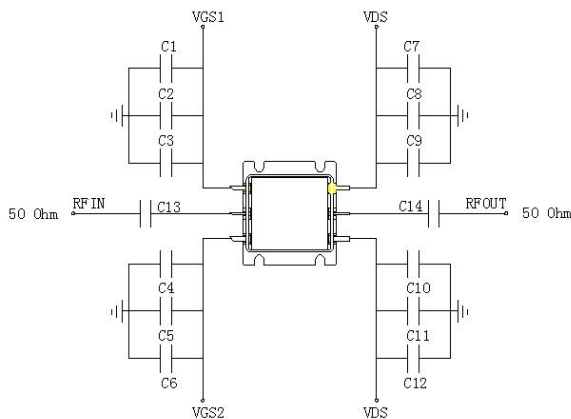
Symbol	Parameter	Value	Remark
Vd	Drain Voltage	36V	
Vg	Grid Voltage	-10V	
Tch	Channel Temperature	200°C	【1】
Tm	Mounting Temperature	300°C	1 min, N2 Protection
Tstg	Storage Temperature	-55~175°C	

【1】 Exceeding any one or combination of these limits may cause permanent damage.

Outline Drawing



Application Circuit



Symbol	Value
C1/C4	100pF
C2/C5	1000pF
C3/C6	10uF
C7/C10	100pF
C8/C11	1000pF
C9/C12	200uF
C13	20pF
C14	20pF

Note:

- (1) This product is an internal matching tube, and the input and output impedance values are both 50 ohms;
- (2) Please strictly follow the order of adding negative electricity first and then positive electricity in the power-on sequence. When de-energizing, first reduce the drain voltage and then reduce the gate voltage;
- (3) This product is a high-power device, and attention should be paid to heat dissipation during use. The higher the case temperature, the shorter the service life, and the operating temperature should not be higher than 70 degrees;
- (4) This product is an electrostatic sensitive device, you need to pay attention to electrostatic protection during storage and use, and you need to be well grounded when using it;
- (5) The input standing wave is relatively high, and the input terminal needs to be connected to an isolator.